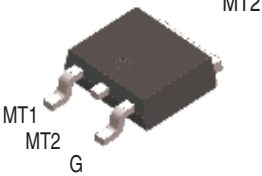
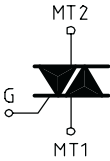


HIGH COMMUTATION TRIAC

DPAK (Plastic)  	<table> <tr> <td>On-State Current</td><td>Gate Trigger Current</td></tr> <tr> <td>4 Amp</td><td>$\leq 35 \text{ mA}$</td></tr> <tr> <td colspan="2">Off-State Voltage</td></tr> <tr> <td colspan="2">$200 \text{ V} \div 800 \text{ V}$</td></tr> </table> This series of TRIACs uses a high performance PNPN technology. These parts are intended for general purpose AC switching applications with highly inductive loads.	On-State Current	Gate Trigger Current	4 Amp	$\leq 35 \text{ mA}$	Off-State Voltage		$200 \text{ V} \div 800 \text{ V}$	
On-State Current	Gate Trigger Current								
4 Amp	$\leq 35 \text{ mA}$								
Off-State Voltage									
$200 \text{ V} \div 800 \text{ V}$									

Absolute Maximum Ratings, according to IEC publication No. 134

SYMBOL	PARAMETER	CONDITIONS	Value	Unit
$I_{T(RMS)}$	RMS On-state Current (full sine wave)	All Conduction Angle, $T_C = 95^\circ\text{C}$	4	A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 60 Hz ($t = 16.7 \text{ ms}$)	33	A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 50 Hz ($t = 20 \text{ ms}$)	30	A
I^2t	Fusing Current	$t_p = 10 \text{ ms}$, Half Cycle	4.5	A^2s
I_{GM}	Peak Gate Current	$20 \mu\text{s max.}$ $T_j = 125^\circ\text{C}$	4	A
$P_{G(AV)}$	Average Gate Power Dissipation	$T_j = 125^\circ\text{C}$	1	W
di/dt	Critical rate of rise of on-state current	$I_G = 2 \times I_{GT}$, $t_r \leq 100\text{ns}$ $f = 120 \text{ Hz}$, $T_j = 125^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
T_j	Operating Temperature		$(-40 + 125)$	$^\circ\text{C}$
T_{stg}	Storage Temperature		$(-40 + 150)$	$^\circ\text{C}$
T_{sld}	Soldering Temperature	10s max	260	$^\circ\text{C}$

SYMBOL	PARAMETER	VOLTAGE					Unit
		B	D	M	S	N	
V_{DRM} V_{RRM}	Repetitive Peak Off State Voltage	200	400	600	700	800	V

HIGH COMMUTATION TRIAC

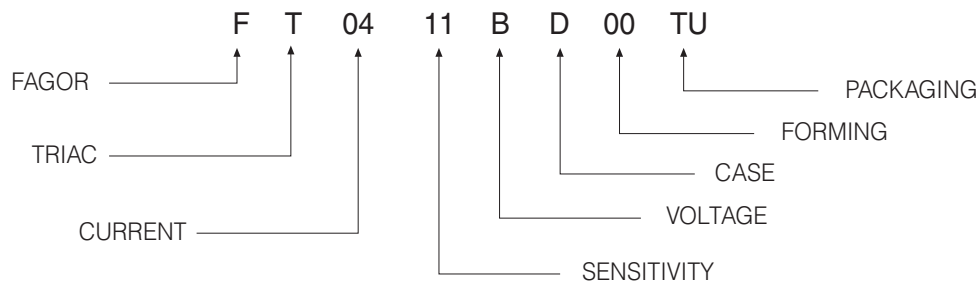
Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	Quadrant		SENSITIVITY		Unit
					11	14	
$I_{GT}^{(1)}$	Gate Trigger Current	$V_D = 12 V_{DC}$, $R_L = 33\Omega$, $T_j = 25^\circ C$	Q1÷Q3	MAX	25	35	mA
V_{GT}	Gate Trigger Voltage	$V_D = 12 V_{DC}$, $R_L = 33\Omega$, $T_j = 25^\circ C$	Q1÷Q3	MAX	1.3		V
V_{GD}	Gate Non Trigger Voltage	$V_D = V_{DRM}$, $R_L = 3.3K\Omega$, $T_j = 125^\circ C$	Q1÷Q3	MIN	0.2		V
$I_H^{(2)}$	Holding Current	$I_T = 100$ mA, Gate open, $T_j = 25^\circ C$		MAX	25	35	mA
I_L	Latching Current	$I_G = 1.2 I_{GT}$, $T_j = 25^\circ C$	Q1, Q3	MAX	40	50	mA
			Q2	MAX	50	60	mA
$dV/dt^{(2)}$	Critical Rate of Voltage Rise	$V_D = 0.67 \times V_{DRM}$, Gate open $T_j = 125^\circ C$		MIN	200	500	V/ μ s
$(dI/dt)^{(2)}$	Critical Rate of Current Rise	$(dv/dt)c = 0.1$ V/ μ s $T_j = 125^\circ C$ $(dv/dt)c = 10$ V/ μ s $T_j = 125^\circ C$ without snubber $T_j = 125^\circ C$		MIN MIN MIN	- - 2.5	- - 3.5	A/ms
$V_{TM}^{(2)}$	On-state Voltage	$I_T = 5.5$ Amp, $t_p = 380$ μ s, $T_j = 25^\circ C$		MAX	1.6		V
$V_{t(o)}^{(2)}$	Threshold Voltage	$T_j = 125^\circ C$		MAX	0.85		V
$r_d^{(2)}$	Dynamic Resistance	$T_j = 125^\circ C$		MAX	140		m Ω
I_{DRM}/I_{RRM}	Off-State Leakage Current	$V_D = V_{DRM}$, $T_j = 125^\circ C$ $V_R = V_{RRM}$, $T_j = 25^\circ C$		MAX MAX	0.5 5		mA μ A
$R_{th(j-c)}$	Thermal Resistance Junction-Case	for AC 360° conduction angle			2.2		°C/W
$R_{th(j-a)}$					70		°C/W

(1) Minimum I_{GT} is guaranteed at 5% of I_{GT} max.

(2) For either polarity of electrode MT2 voltage with reference to electrode MT1.

PART NUMBER INFORMATION



HIGH COMMUTATION TRIAC

Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle)

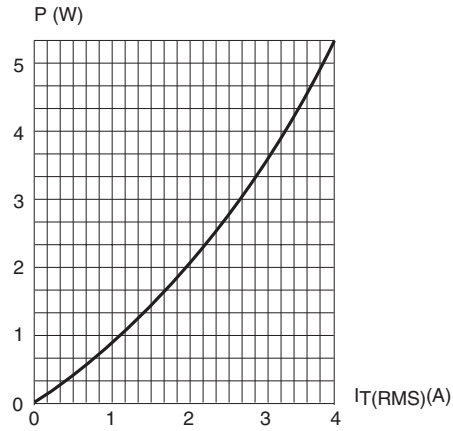


Fig. 2: RMS on-state current versus case temperature (full cycle)

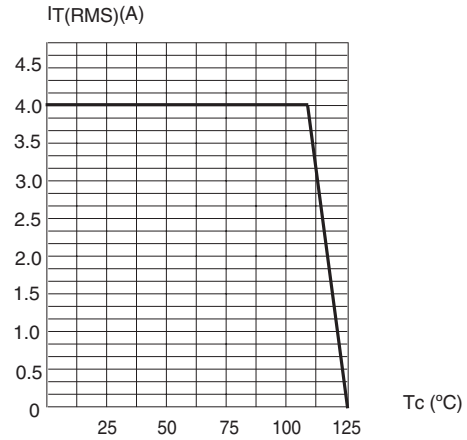


Fig. 3: Relative variation of thermal impedance versus pulse duration

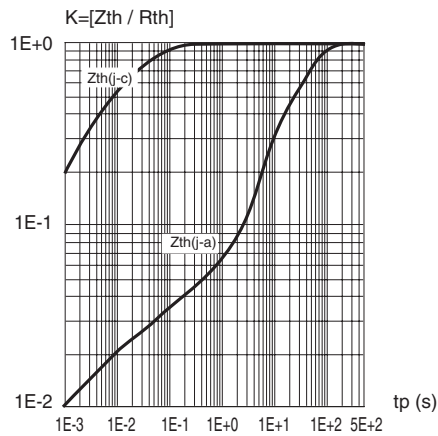


Fig. 4: On-state characteristics (maximum values)

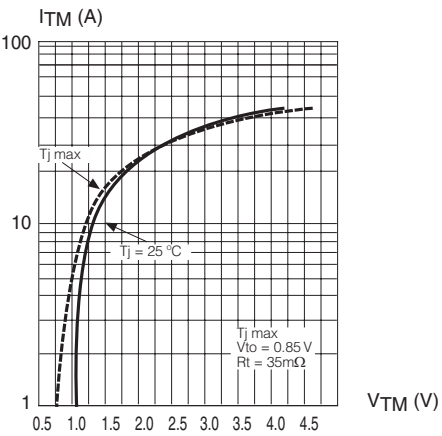


Fig. 5: Surge peak on-state current versus number of cycles

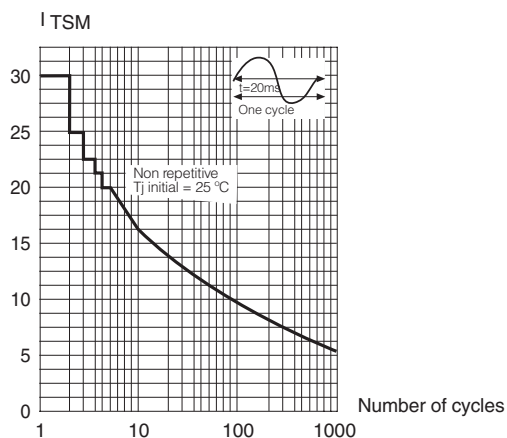
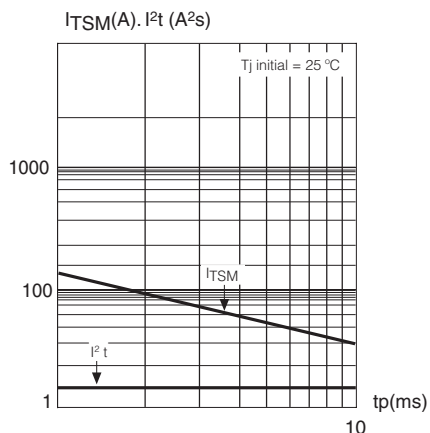


Fig. 6: Non repetitive surge peak on-state current for a sinusoidal pulse with width: $t_p < 10 ms$, and corresponding value of $I^2 t$.



HIGH COMMUTATION TRIAC

Fig. 7: Relative variation of gate trigger current, holding current and latching versus junction temperature (typical values)

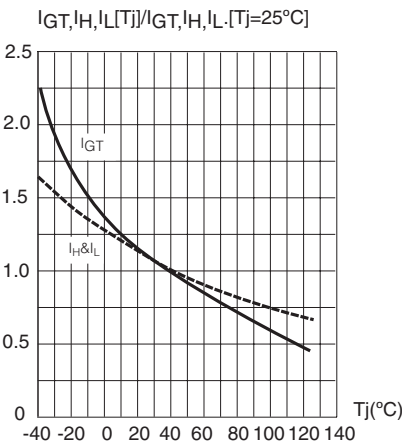
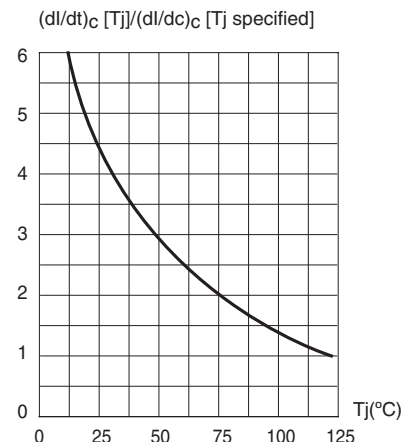
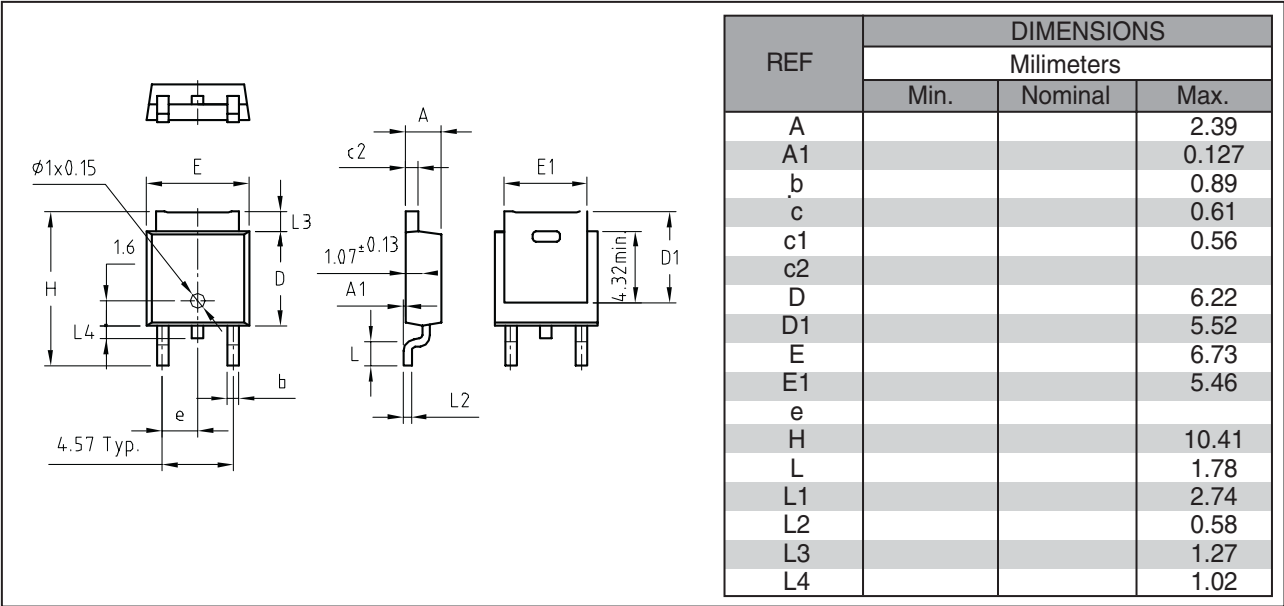


Fig. 8: Relative variation of critical rate of decrease of main current versus junction temperature



PACKAGE MECHANICAL DATA

DPAK TO



Marking: type number
Weight: 0.2 g